

E-beam Resist 제품 리스트

제품에 따라 용량 50, 100, 150, 250ml 등 다양한 용량 선택 가능하며, 관련 developer, remover를 취급하고 있습니다.

Type	Product	TF (μm) 4000 rpm	Characteristic Properties	Application	Resolution [nm]	Con- trast	Expo- sure	Thinner	Developer	Remover
Positive resist	AR-P 617	0.09 – 1.7	Copolymer, highest resol., 2x more sensitiver than PMMA, lift-off	ICs, masks	10 / 100	6.0	e-beam dee UV	600-07	600-50 600-55	600-71 600-76
	PMMA * (anisole)	0.03 – 2.0	950K, 495K, 350K, 120K, 35K, high resolution	ICs, masks	6 / 100	7.0		Anisole	PMMA- Dev series	Acetone KOH
	AR-P 631-671 (chlorobenzene)	0.02 – 1.7	950K, 600K, 200K, 50K highest resol., process stable	ICs, masks	6 / 100	7.0		600-01	600-55 600-56	600-71 300-76
	AR-P 639-679 (ethyl lactate)	0.02 – 0.7	950K, 600K, 200K, 50K highest resol., process stable	ICs, masks	6 / 100	7.0		600-09	300-55 300-56	600-71 300-76
	SML Resist *	0.05 – 2.0	Very high resolution and aspect ratio, slow etch rate	ICs, masks	5 / 20	7.8		N/A	MIBK, IPA, DI water	Acetone
	AR-P 6200 CSAR 62	0.08; 0.4; 0.2; 0.8	Highest resol., high sensitivity, plasma etching-resistant	ICs, sensors, masks	6	15		600-02	600-546 600-548 600-549	600-71 300-76
	AR-P 6500	350 rpm: 28, 56, 88, 135	Thick PMMA films up to 250 μm for MST, synchrotron	Micro components	1 μm (x-ray)	10 (x-ray)	x-ray, e-beam	300-12	600-51 600-56	600-71 300-76
	AR-P 7400	0.1; 0.4	Mix&match, high resol., plasma etching- resistant, also neg.	ICs, masks	40 / 150	4.0	e-beam dee UV g-line i-line	300-12	300-47	600-71 300-73
Negative resist	AR-N 7500	0.1; 0.4	Mix&match, high resol., plasma etching- resistant, pos./neg.	ICs, masks	40 / 100	5.0		300-12	300-47	600-71 300-73
	AR-N 7520 new	0.1; 0.2; 0.4	Mix&match, highly sensitive, highest resolution	ICs, masks	30	8.0	e-beam dee UV i-line	300-12	300-46 300-47	600-71 300-73
	AR-N 7520	0.1; 0.4	Mix&match, highest resolution, high precision edges	ICs, masks	28	10.0		300-12	300-47	300-76 300-73
	AR-N 7700	0.1; 0.4	CAR, high resolution, high sensitivity, steep gradation	ICs, masks	80 / 100	5.0	e-beam dee UV	300-12	300-46 300-47	300-76 300-73
	AR-N 7720	0.25; 1.4	CAR, high resolution, flat gradation for 3- dimens. struct.	Diffract. optics	80 / 200	< 1.0		300-12	300-46 300-47	300-76 300-72
Special application	DisCharge H2O	0.04 (at 1000 RPM)	Anti-charging agent used in electron-beam lithography to prevent charge accumulation on electrically insulated substrates (Novolac resist, PMMA, HSQ, mr-PosEBR, CSAR62, ZEP520A)					-	-	DI water
	SurPass	-	Adhesion promoter / Priming Agent through cationic interaction and modification of the substrate surface energy							DI water or IPA
	AR 300-80 HMDS	0.015; 0.005	Adhesion promoter	-	-	-	-	-	-	600-70 600-71
	AR-PC 503, dyed 504, 5040	1.2; 2.2	protective coating, 40% KOH etch-stable	Protective film	-	-	-	600-01	-	600-71 300-76
	AR-BR 5460, 5480	1; 0.5	bottom resist for 2L lift- off	Lift-off (pos./neg.)	3; 1.5	lift-off	-	-	-	300-76 300-73

PMMA

500ml 이상 구매 시 molecular weight, dilutions별로 250ml씩 선택 가능.

예) PMMA 1 liter 구매 시,

- 1). PMMA 950K A4: 250 ml x 1 bottle.
- 2). PMMA 495K A6: 500 ml x 1 bottle.
- 3). PMMA 120K A8: 250 ml x 1 bottle.

SML Resist

100ml 이상 구매 시 thickness 별로 50ml씩 선택 가능.

예) SML resist 200 ml 구매 시,

- 1). SML100: 50 ml x 1 bottle.
- 2). SML300: 100 ml x 1 bottle.
- 3). SML2000: 50 ml x 1 bottle.